PDTC144WMB



NPN resistor-equipped transistor; R1 = 47 k Ω , R2 = 22 k Ω Rev. 1 — 2 July 2012 Product data s

Product data sheet

1. **Product profile**

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA144WMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------|------------------------------|--------------------------|------|------|------|------|
| V_{CEO} | collector-emitter voltage | open base | - | - | 50 | V |
| Io | output current | | - | - | 100 | mA |
| R1 | bias resistor 1 (input) | T _{amb} = 25 °C | 33 | 47 | 61 | kΩ |
| R2/R1 | bias resistor ratio | | 0.37 | 0.47 | 0.57 | |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------|------------------------|----------------|
| 1 | I | input (base) | | |
| 2 | G | GND (emitter) | 1 | <u> </u> |
| 3 | 0 | output (collector) | 2 Transparent top view | 1 R1 R2 |
| | | | DFN1006B-3 (SOT883B) | sym007 2 |

3. Ordering information

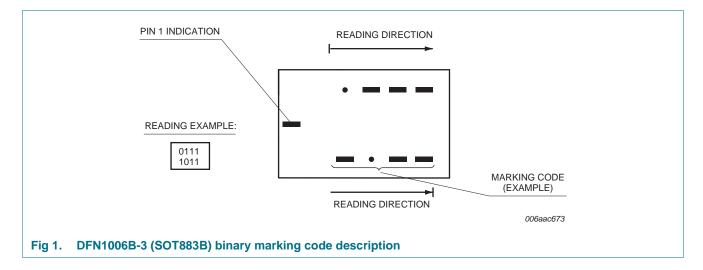
Table 3. Ordering information

| Type number | Package | | |
|-------------|------------|--|---------|
| | Name | Description | Version |
| PDTC144WMB | DFN1006B-3 | Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm | SOT883B |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PDTC144WMB | 0011 1111 |



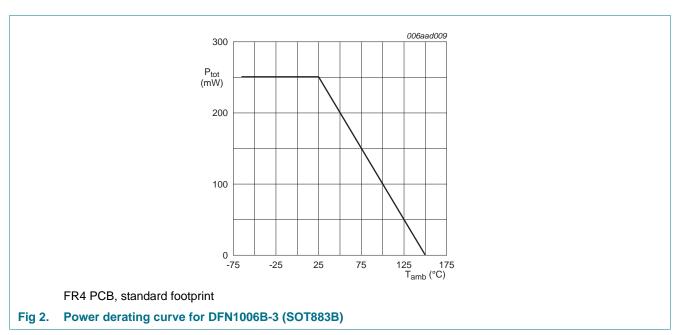
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------|------------|-----|-----|------|
| V_{CBO} | collector-base voltage | open emitter | | - | 50 | V |
| V_{CEO} | collector-emitter voltage | open base | | - | 50 | V |
| V_{EBO} | emitter-base voltage | open collector | | - | 10 | V |
| VI | input voltage | positive | | - | 40 | V |
| | | negative | | - | -10 | V |
| I _O | output current | | | - | 100 | mA |
| I _{CM} | peak collector current | pulsed; t _p ≤ 1 ms | | - | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | <u>[1]</u> | - | 250 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

Table 6. Thermal characteristics

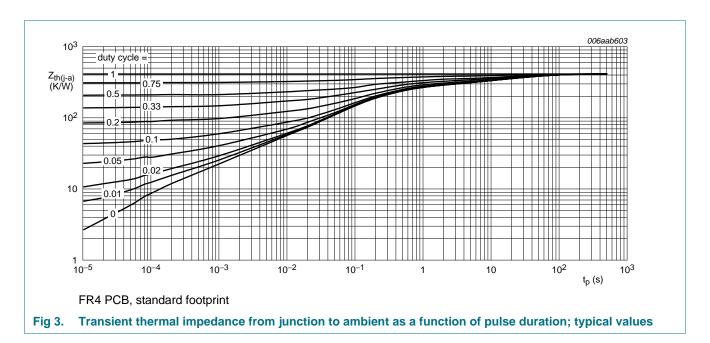
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|---|-------------|------------|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | <u>[1]</u> | - | - | 500 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PDTC144WMB

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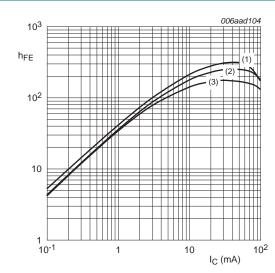


7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|--------------------------------------|--|------------|------|------|------|------|
| I _{CBO} | collector-base cut-off current | $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | | - | - | 100 | nA |
| I _{CEO} | collector-emitter cut-off | V_{CE} = 30 V; I_{B} = 0 A; T_{amb} = 25 °C | | - | - | 1 | μΑ |
| | current | $V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$ | | - | - | 5 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | | - | - | 110 | μΑ |
| h _{FE} | DC current gain | $V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 \text{ °C}$ | | 60 | - | - | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$ | | - | - | 150 | mV |
| V _{I(off)} | off-state input voltage | V_{CE} = 5 V; I_{C} = 100 μ A; T_{amb} = 25 °C | | - | 1.7 | 1.2 | V |
| V _{I(on)} | on-state input voltage | $V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$ | | 4 | 2.7 | - | V |
| R1 | bias resistor 1 (input) | T _{amb} = 25 °C | | 33 | 47 | 61 | kΩ |
| R2/R1 | bias resistor ratio | | | 0.37 | 0.47 | 0.57 | |
| C _C | collector capacitance | $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$ | | - | - | 2.5 | pF |
| f_{T} | transition frequency | $V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA; } f = 100 \text{ MHz;}$ $T_{amb} = 25 \text{ °C}$ | <u>[1]</u> | - | 230 | - | MHz |

^[1] Characteristics of built-in transistor.



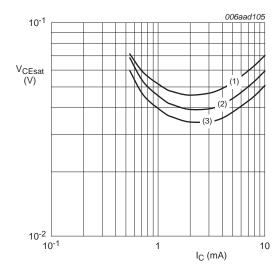
 $V_{CE} = 5 V$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



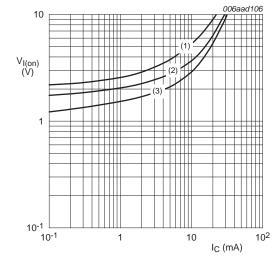
 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values

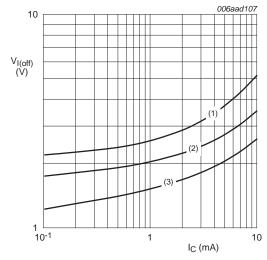


 $V_{CE} = 0.3 \text{ V}$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



 $V_{CE} = 5 \text{ V}$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

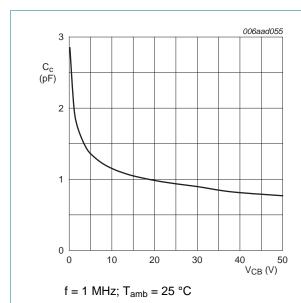


Fig 8. Collector capacitance as a function of collector-base voltage; typical values of built-in transistor

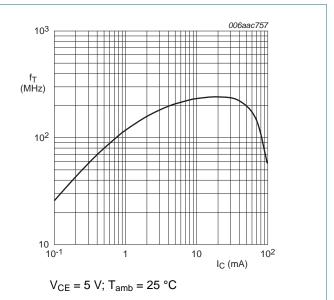


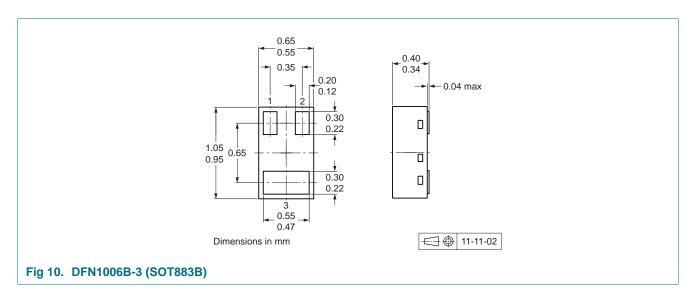
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

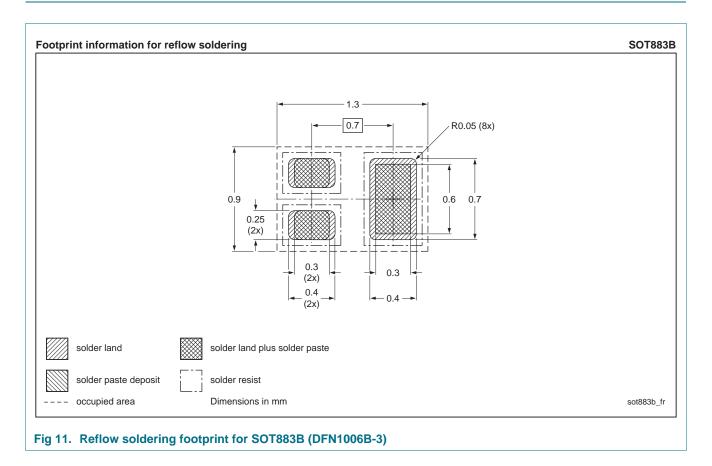
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PDTC144WMB v.1 | 20120702 | Product data sheet | - | - |

12. Legal information

12.1 Data sheet status

| Document status[1] [2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC144WMB

NPN resistor-equipped transistor; R1 = 47 k Ω , R2 = 22 k Ω

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